General purpose transistor (dual transistors)

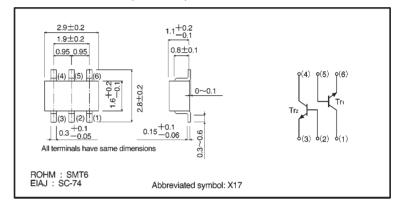
Features

- Two 2SD1484K chips in an SMT package.
- Mounting possible with SMT3 automatic mounting machine.
- Transistor elements are independent, eliminating interference.
- 4) High collector current.Ic = 500mA
- 5) Mounting cost and area can be cut in half.

StructureEpitaxial planar typeNPN silicon transistor

The following characteristics apply to both Tr₁ and Tr₂.

●External dimensions (Units: mm)



● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	60	V	
Collector-emitter voltage	Vceo	50	V	
Emitter-base voltage	VEBO	5	V	
Collector current	lc	500	mA	
Power dissipation	Pd	300 (TOTAL)	mW *	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	− 55∼ + 150	Č	

*200 mW per element must not be exceeded.

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●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	60	_	_	٧	Ic=100 μ A	
Collector-emitter breakdown voltage	BVceo	50	_	_	٧	Ic=1mA	
Emitter-base breakdown voltage	ВУЕВО	5	_	_	V	l∈=100 μ A	
Collector cutoff current	Ісво	_	_	0.1	μΑ	Vcb=30V	
Emitter cutoff current	ІЕВО	_	_	0.1	μΑ	V _{EB} =4V	
Collector-emitter saturation voltage	VCE(sat)	_	_	0.6	٧	Ic/Iв=500mA/50mA	
DC current transfer ratio	hfe	120	_	390	_	VcE=3V, Ic=100mA	*
Transition frequency	fτ	_	250	_	MHz	VcE=5V, IE=-20mA, f=100MHz	
Output capacitance	Cob	_	7	_	pF	VcB=10V, IE=0A, f=1MHz	

^{*} Measured using pulse current.

Packaging specifications

	Packaging type	Taping
	Code	T110
Part No.	Basic ordering unit (pieces)	3000
IMX17		0

Electrical characteristic curves

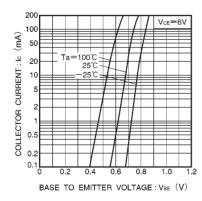


Fig.1 Grounded emitter propagation characteristics

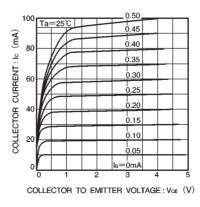


Fig.2 Grounded emitter output characteristics

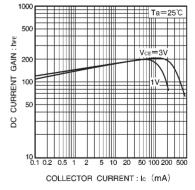


Fig.3 DC current gain vs. collector current (I)

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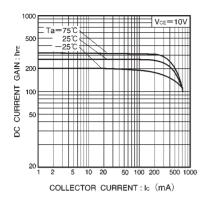


Fig.4 DC current gain vs. collector current (II)

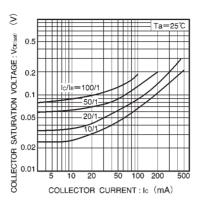


Fig.5 Collector-emitter saturation voltage vs. collector current

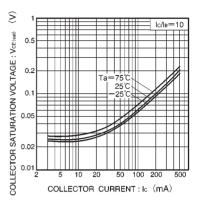


Fig.6 Collector-emitter saturation voltage vs. collector current

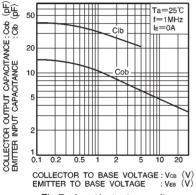


Fig.7 Input/output capacitance vs. voltage

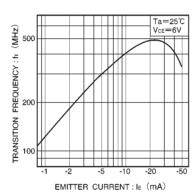


Fig.8 Gain bandwidth product vs. emitter current